

PMZB290UN

20 V, single N-channel Trench MOSFET **20 January 2016**

Product data sheet

1. **General description**

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. **Features and benefits**

- Fast switching
- Trench MOSFET technology
- Low threshold voltage
- Ultra thin package profile with 0.37 mm height
- ElectroStatic Discharge (ESD) protection: 2 kV HBM

Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	1	Α
Static characteristics					,		
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 200 mA; T_j = 25 °C		-	290	350	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa255

6. Ordering information

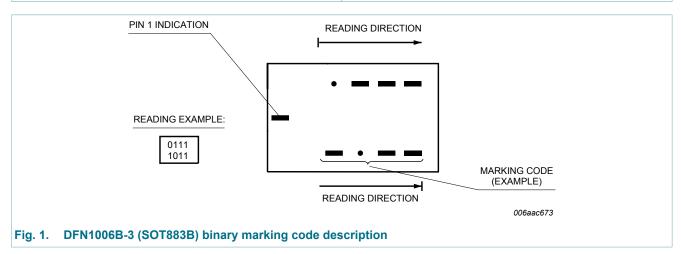
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMZB290UN	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZB290UN	0000 0101



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	1	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	liode					
Is	source current	T _{amb} = 25 °C	[1]	-	0.67	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

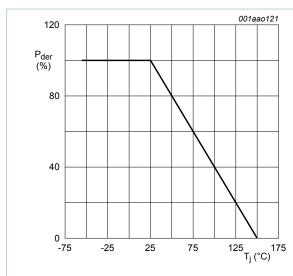


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

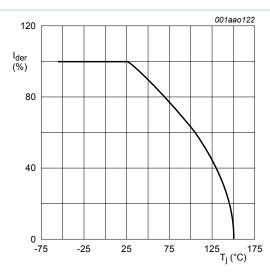


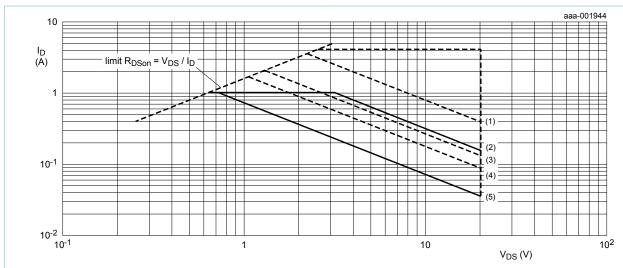
Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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I_{DM} is single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) DC; T_{sp} = 25 °C
- (3) $t_p = 10 \text{ ms}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from ju	thermal resistance		[1]	-	305	360	K/W
	from junction to ambient		[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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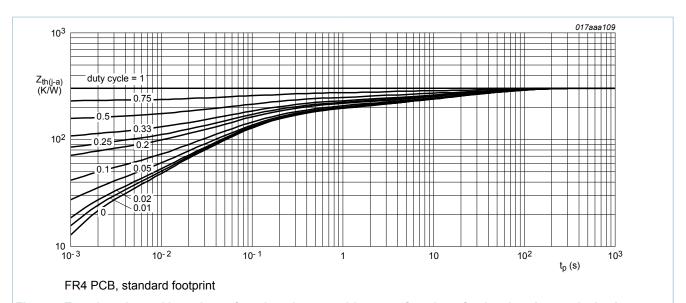


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

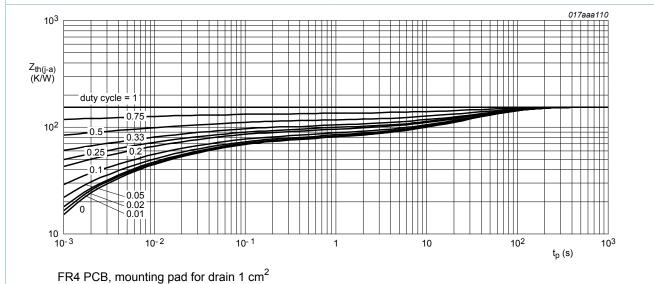


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

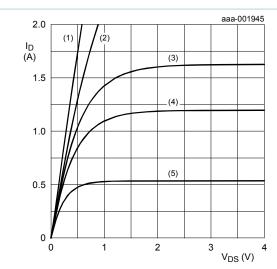
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.45	0.7	0.95	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I_{D} = 200 mA; T_{j} = 25 °C	-	290	350	mΩ
re	resistance	V _{GS} = 4.5 V; I _D = 200 mA; T _j = 150 °C	-	460	560	mΩ
		V _{GS} = 2.5 V; I _D = 100 mA; T _j = 25 °C	-	360	450	mΩ
		V _{GS} = 1.8 V; I _D = 75 mA; T _j = 25 °C	-	460	650	mΩ
9fs	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	5.8	-	S
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 10 V; I _D = 1 A; V _{GS} = 4.5 V;	-	0.89	1.2	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.13	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 20 V; f = 1 MHz; V _{GS} = 0 V;	-	45	68	pF
C _{oss}	output capacitance	T _j = 25 °C	-	11	-	pF
C _{rss}	reverse transfer capacitance		-	7	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; R_L = 10 Ω ; V_{GS} = 4.5 V;	-	4.5	9	ns
t _r	rise time	$R_{G(ext)}$ = 6 Ω; T_j = 25 °C	-	10	-	ns
t _{d(off)}	turn-off delay time		-	18.5	37	ns
t _f	fall time		-	5	-	ns
Source-drai	in diode		<u> </u>	1	-	
V_{SD}	source-drain voltage	$I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.75	1.2	V
		I I				

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$$T_i = 25 \,^{\circ}C$$

(1)
$$V_{GS} = 4.5 \text{ V}$$

$$(2) V_{GS} = 2.5 V$$

(3)
$$V_{GS} = 2.0 \text{ V}$$

$$(4) V_{GS} = 1.8 V$$

$$(5) V_{GS} = 1.5 V$$

Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

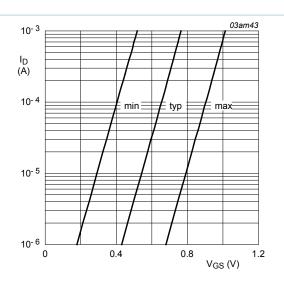
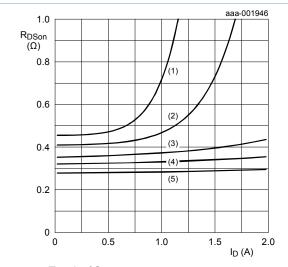


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; V_{DS} = 5V$$



$$T_j = 25 \,^{\circ}C$$

(1)
$$V_{GS} = 1.8 \text{ V}$$

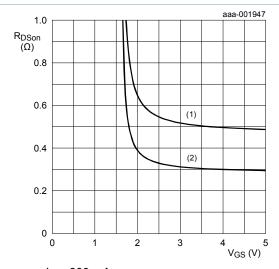
(2)
$$V_{GS} = 2 V$$

$$(3) V_{GS} = 2.5 V$$

(4)
$$V_{GS} = 3 V$$

$$(5) V_{GS} = 4.5 V$$

Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 800 \text{ mA}$

(1)
$$T_i = 150 \, ^{\circ}\text{C}$$

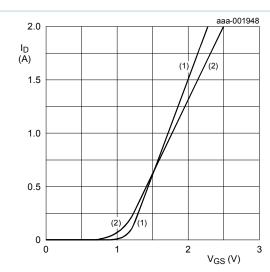
(2)
$$T_i = 25 \, ^{\circ}C$$

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ (1) $T_j = 25 \text{ °C}$

(2) $T_j = 150 \, ^{\circ}C$

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

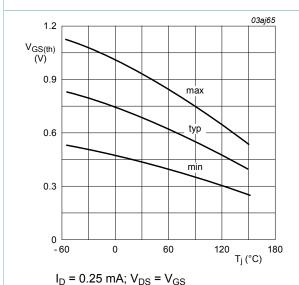


Fig. 13. Gate-source threshold voltage as a function of

junction temperature

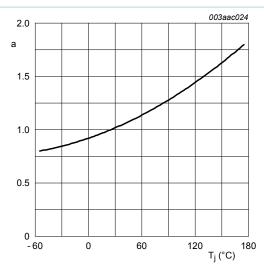


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

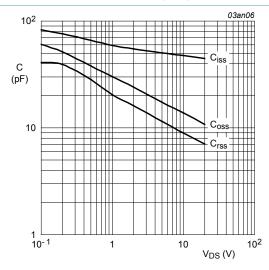


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

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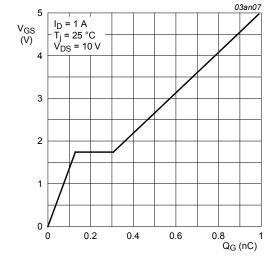


Fig. 15. Gate-source voltage as a function of gate charge; typical values

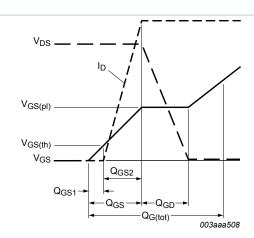
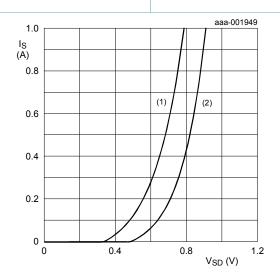


Fig. 16. Gate charge waveform definitions



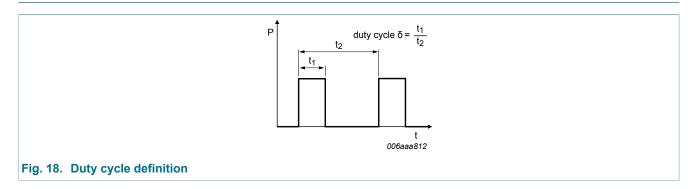
 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$ (2) $T_i = 25 \,^{\circ}C$

Fig. 17. Source current as a function of source-drain voltage; typical values

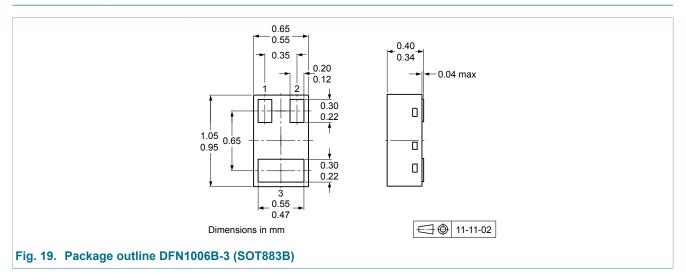
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11. Test information

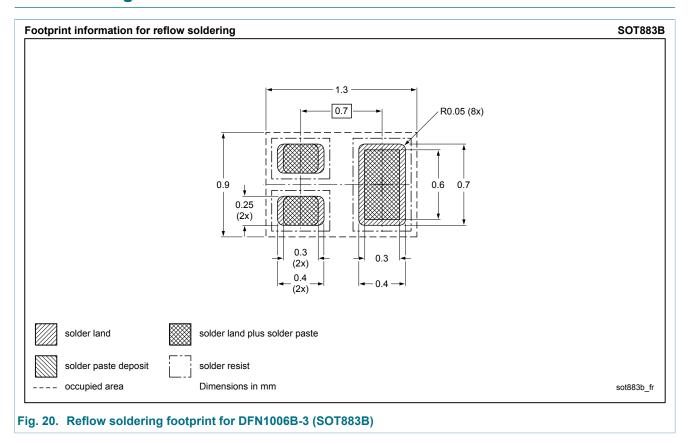


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMZB290UN v.2	20160120	Product data sheet	-	PMZB290UN v.1		
Modifications:	values for gate leakage current and forward transconductance changed					
PMZB290UN v.1	20120511	Product data sheet	-	-		

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15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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